



INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY DOCKET NO. ITL1027US (P16711)	SERIAL NO. 10/698,204
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U.S. PATENT DOCUMENTS

EXAMINE R INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
	A.						
	B.						
	C.						
	D.						
	E.						
	F.						
	G.						
	H.						
	I.						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	J.							
	K.							
	L.							
	M.							
	N.							
	O.							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>me</i>	P.	Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf
<i>me</i>	Q.	Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at http://www.semtech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf
	R.	
	S.	
	T.	

EXAMINER <i>Michelle Estrada</i>	DATE CONSIDERED <i>9/27/04</i>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	